具有可控接通功能的 TPS22930 超小型、低导通电阻负载开关

1 特性

- 集成单通道负载开关
- 超小型 4 端子 Wafer-Chip-Scale Package（显示了标称尺寸 - 详情请见附录）
  - 0.9mm × 0.9mm、0.5mm 间距、0.5mm 高度 (YZV)
- 输入电压范围：1.4V 至 5.5V
- 超低 R_{ON} 电阻
  - V_{IN} = 5V 时，R_{ON} = 35mΩ
  - V_{IN} = 3.6V 时，R_{ON} = 36mΩ
  - V_{IN} = 1.8V 时，R_{ON} = 49mΩ
- 2A 最大持续开关电流
- 低静态电流（小于 3μA）
- 低控制输入阈值支持使用 1.2V/1.8V/2.5V/3.3V 逻辑
- 受控转换率
- 欠压锁定
- 禁用时，反向电流保护

2 应用

- 智能手机/无线听筒
- 便携式工业/医疗设备
- 便携式媒体播放器
- POS 机终端
- 全球卫星定位系统 (GPS) 导航器件
- 数码摄像机
- 便携式仪表

3 说明

TPS22930 是一款小型、低 R_{ON} 负载开关，具有可控导通功能。此器件包括一个 P 沟道 MOSFET，可在 1.4V 至 5.5V 的输入电压范围内运行。此开关由一个开/关输入 (ON) 控制，此输入能够与低压控制信号直接相连。TPS22930 高电平使能。

TPS22930 器件通过在反向电压（也称为反向电流）情况下禁用体二极管来提供电路断路器功能。只有当电源开关被禁用时（关闭）反向电流保护才被激活。当输出电压 (V_{OUT}) 被驱动至高于输入 (V_{IN}) 时，此器件释放体二极管来停止流向开关输入一侧的电流。此外，如果此输入电压过低，欠压锁定 (UVLO) 保护会将此开关关闭。

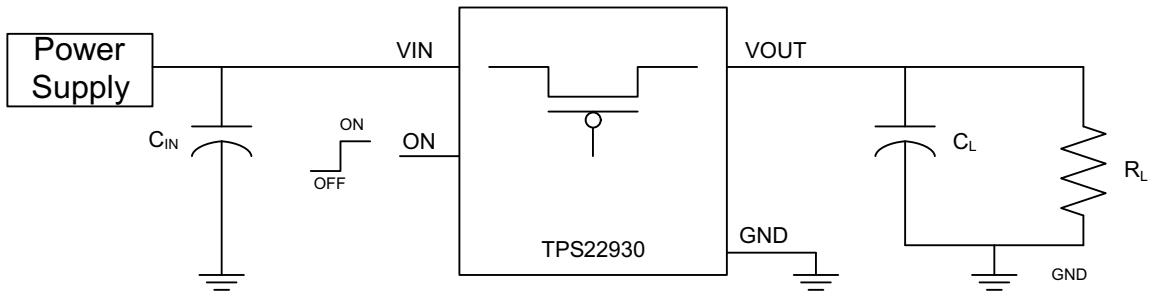
为了避免涌入电流，此器件的转换率由内部控制。

TPS22930 采用超小型、节省空间的 4 引脚 CSP 封装并可在 -40°C 至 85°C 的自然通风温度范围内运行。

器件信息(1)

器件型号	封装	封装尺寸（最大值）
TPS22930	DSBGA (4)	0.92mm × 0.92mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化版原理图

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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (February 2016) to Revision C (January 2021) — **Page**

- 更新了整个文档的表、图和交叉参考的编号格式 1

Changes from Revision A (June 2015) to Revision B (February 2016) — **Page**

- 更改了 *引脚配置和功能* 1

Changes from Revision * (November 2012) to Revision A (June 2015) — **Page**

- 删除了“订购信息”表 1
- 添加了“ESD 等级”表、“特性说明”部分、“器件功能模式”、“应用和实施”部分、“电源相关建议”部分、“布局”部分、“器件和文档支持”部分以及“机械、封装和可订购信息”部分 1

5 Pin Configuration and Functions

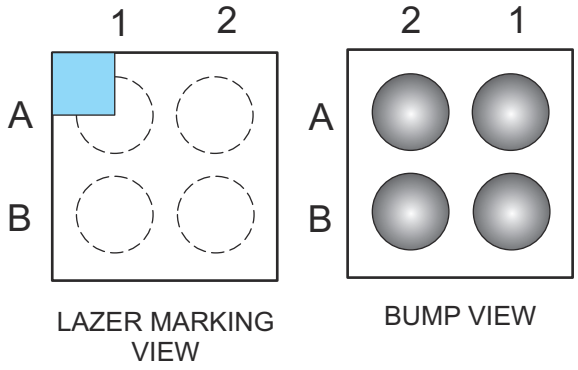


图 5-1. YZV PACKAGE 4-Pin DSBGA Bottom View

表 5-1. Pin Assignments

A	VOUT	VIN
B	GND	ON
	1	**2**

表 5-2. Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
A1	VOUT	O	Switch output.
A2	VIN	I	Switch input. Input bypass capacitor recommended for minimizing V_{IN} dip during transients.
B1	GND	–	Device ground.
B2	ON	I	Switch control input, active high. Do no leave floating.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	MAX	UNIT
V_{IN}	Input voltage	–0.3	6	V
V_{OUT}	Output voltage	–0.3	6	V
V_{ON}	Input voltage	–0.3	6	V
I_{MAX}	Maximum continuous switch current		2	A
I_{PLS}	Maximum pulsed switch current, pulse ≤1ms, 25% duty cycle		2.5	A
T_A	Operating free-air temperature (3)	–40	85	°C
T_J	Maximum junction temperature		150	°C
T_{stg}	Storage temperature	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal.
(3) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature [$T_{A(max)}$] is dependent on the maximum operating junction temperature [$T_{J(max)}$], the maximum power dissipation of the device in the application [$P_{D(max)}$], and the junction-to-ambient thermal resistance of the part/package in the application ($R_{\theta JA}$), as given by the following equation: $T_{A(max)} = T_{J(max)} - (R_{\theta JA} \times P_{D(max)})$

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{IN}	Input voltage range		1.4	5.5	V
V_{ON}	ON voltage range		0	5.5	V
V_{OUT}	Output voltage range		0	V_{IN}	V
V_{IH}	High-level input voltage, ON	V_{IN} = 3.61 V to 5.5 V	1.1	5.5	V
		V_{IN} = 1.4 V to 3.6V	1.1	5.5	
V_{IL}	Low-level input voltage, ON	V_{IN} = 3.61 V to 5.5 V	0	0.6	V
		V_{IN} = 1.4 V to 3.6 V	0	0.4	
C_{IN}	Input capacitor		1(1)		µF

(1) Refer to 节 9.1 section.

6.4 Thermal Information

THERMAL METRIC(1)		TPS22930 YZV (DSBGA) 4 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	189.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	1.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	36.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	11.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	36.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	–	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

Unless otherwise note, the specification in the following table applies over the operating ambient temperature **–40°C ≤ T_A ≤ 85°C** (Full). Typical values are for T_A = 25°C.

PARAMETER		TEST CONDITIONS		T_A	MIN	TYP	MAX	UNIT
POWER SUPPLIES AND CURRENTS								
I_{IN}	Quiescent current	I_{OUT} = 0 V, V_{IN} = V_{ON} = 5.25 V		Full		2.3	10	µA
		I_{OUT} = 0 V, V_{IN} = V_{ON} = 4.2 V				2.2	7	
		I_{OUT} = 0 V, V_{IN} = V_{ON} = 3.6 V				2.1	7	
		I_{OUT} = 0 V, V_{IN} = V_{ON} = 2.5 V				1.0	5	
		I_{OUT} = 0 V, V_{IN} = V_{ON} = 1.5 V				0.8	5	
$I_{IN(off)}$	Off supply current	V_{OUT} = Open, V_{IN} = 5.25 V, V_{ON} = 0 V		Full		0.3	10	µA
		V_{OUT} = Open, V_{IN} = 4.2 V, V_{ON} = 0 V				0.2	7	
		V_{OUT} = Open, V_{IN} = 3.6 V, V_{ON} = 0 V				0.2	7	
		V_{OUT} = Open, V_{IN} = 2.5 V, V_{ON} = 0 V				0.1	5	
		V_{OUT} = Open, V_{IN} = 1.5 V, V_{ON} = 0 V				0.1	5	
$I_{IN(leak)}$	Leakage current	V_{OUT} = 0 V, V_{IN} = 5.25 V, V_{ON} = 0 V		Full		0.8	10	µA
		V_{OUT} = 0 V, V_{IN} = 4.2 V, V_{ON} = 0 V				0.2	7	
		V_{OUT} = 0 V, V_{IN} = 3.6 V, V_{ON} = 0 V				0.2	7	
		V_{OUT} = 0 V, V_{IN} = 2.5 V, V_{ON} = 0 V				0.1	5	
		V_{OUT} = 0 V, V_{IN} = 1.5 V, V_{ON} = 0 V				0.1	5	
I_{ON}	ON pin input leakage current	V_{ON} = 5.5 V		Full			0.5	µA
$I_{RCP(leak)}$	Reverse leakage current	V_{IN} = V_{ON} = GND, V_{OUT} = 5 V, measured from V_{IN}		Full			2	
UVLO	Undervoltage lockout	V_{IN} increasing, VON = 3.6 V, IOUT = – 100 mA		Full			1.2	
		V_{IN} decreasing, VON = 3.6 V, IOUT = – 100 mA			0.5			
RESISTANCE CHARACTERISTICS								
R_{ON}	ON-state resistance	I_{OUT} = – 200 mA	V_{IN} = 5.0 V	25°C		35	44	mΩ
				Full			50	
			V_{IN} = 4.2 V	25°C		35	44	
				Full			50	
			V_{IN} = 3.6 V	25°C		36	44	
				Full			50	
			V_{IN} = 2.5 V	25°C		39	44	
				Full			50	
			V_{IN} = 1.8 V	25°C		49	55	
				Full			62	
			V_{IN} = 1.5 V	25°C		59	66	
				Full			74	

6.6 Switching Characteristics

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IN} = 5.5 V, T_A = 25°C (unless otherwise noted)						
t_{ON}	Turn-on time	R_L = 10 Ω, C_L = 0.1 µF		4.8		µs
t_{OFF}	Turn-off time			6.3		
t_R	V_{OUT} rise time			5.6		
t_F	V_{OUT} fall time			2.8		
V_{IN} = 4.2 V, T_A = 25°C (unless otherwise noted)						
t_{ON}	Turn-on time	R_L = 10 Ω, C_L = 0.1 µF		5.8		µs
t_{OFF}	Turn-off time			7.3		
t_R	V_{OUT} rise time			5.4		
t_F	V_{OUT} fall time			2.8		
V_{IN} = 3.0 V, T_A = 25°C (unless otherwise noted)						
t_{ON}	Turn-on time	R_L = 10 Ω, C_L = 0.1 µF		7.4		µs
t_{OFF}	Turn-off time			9.5		
t_R	V_{OUT} rise time			6.3		
t_F	V_{OUT} fall time			2.9		

6.7 Typical Characteristics

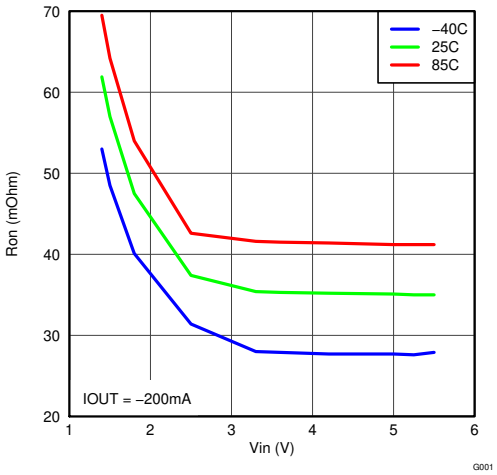


图 6-1. R_{ON} vs V_{IN}

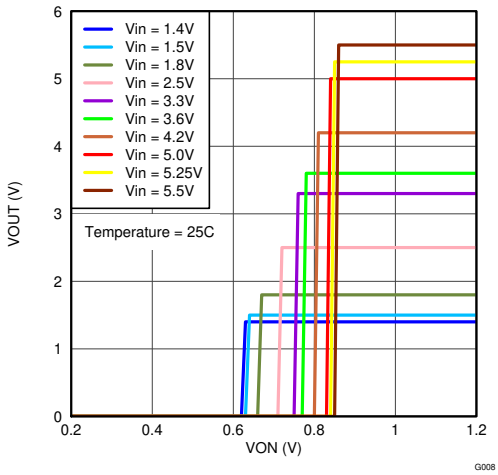


图 6-2. On Input Threshold

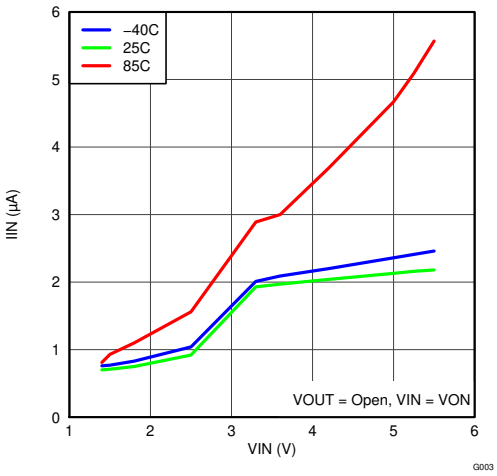


图 6-3. I_{IN} vs V_{IN}

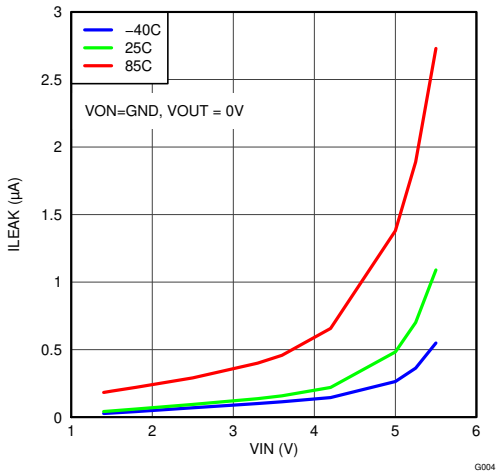


图 6-4. $I_{IN(leak)}$ vs V_{IN}

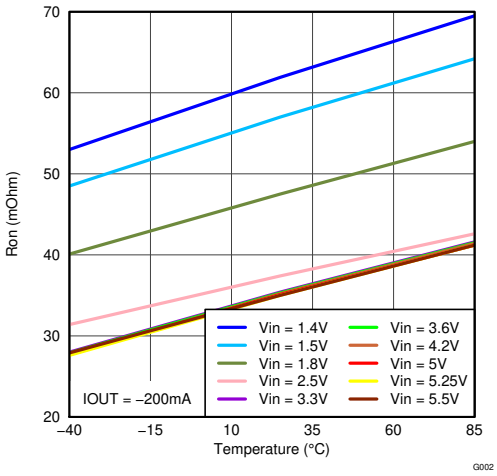


图 6-5. Temperature vs R_{ON}

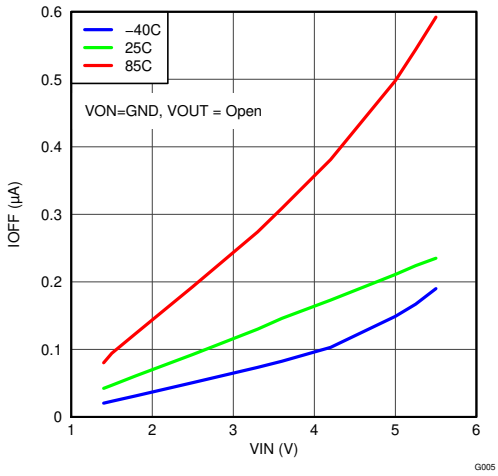


图 6-6. $I_{IN(off)}$ vs V_{IN}

6.7 Typical Characteristics (continued)

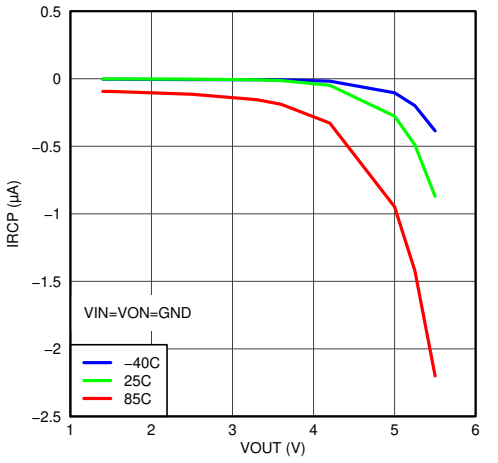


图 6-7. $I_{RCP(leak)}$ vs V_{OUT} (Measured On VIN)

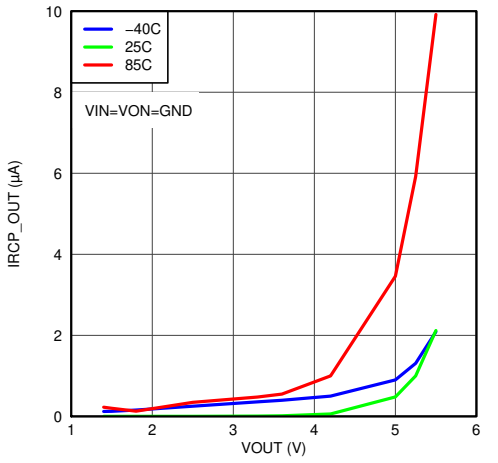


图 6-8. $I_{RCP(leak)}$ vs V_{OUT} (Measured on VOUT)

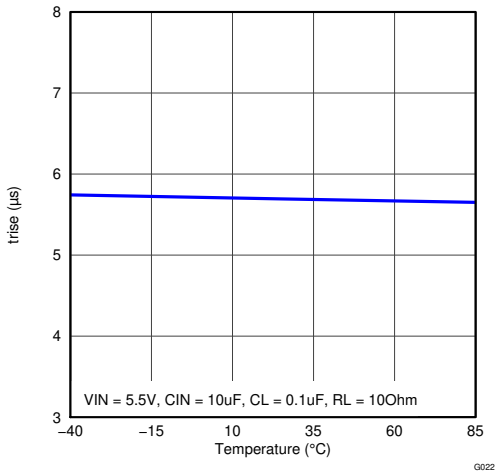


图 6-9. t_R vs Temperature (V_{IN} = 5.5 V)

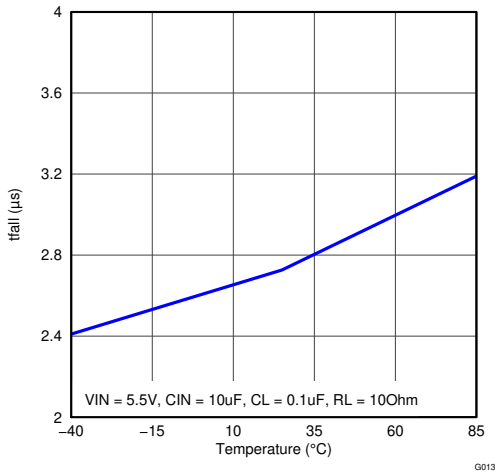


图 6-10. t_F vs Temperature (V_{IN} = 5.5 V)

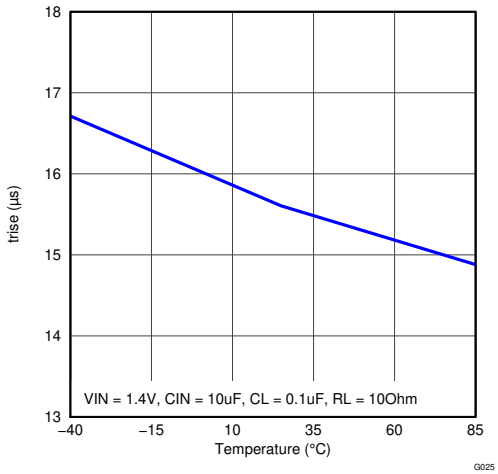


图 6-11. t_R vs Temperature (V_{IN} = 1.4 V)

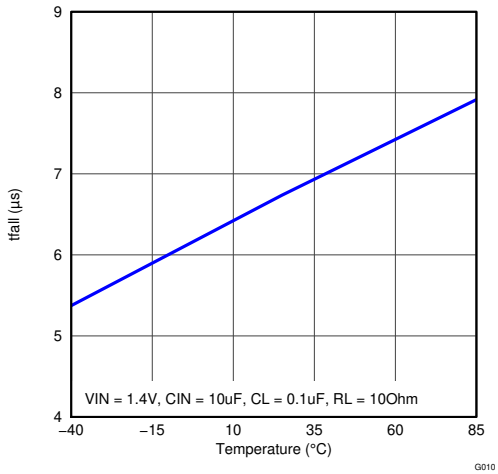


图 6-12. t_F vs Temperature (V_{IN} = 1.4 V)

6.7 Typical Characteristics (continued)

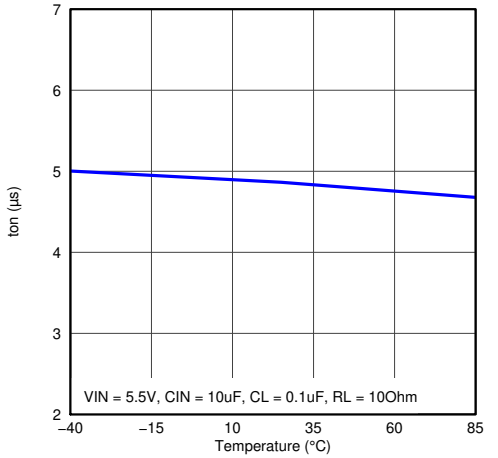


图 6-13. t_{ON} vs Temperature (V_{IN} = 5.5 V)

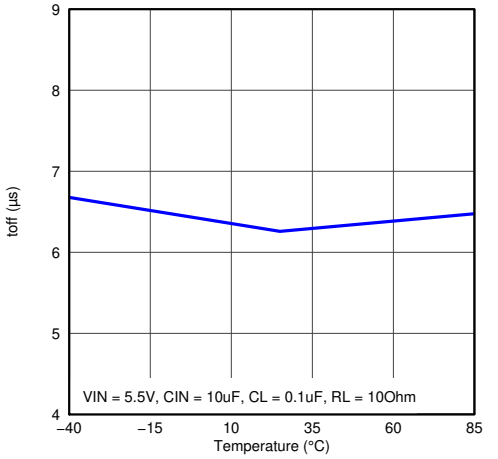


图 6-14. t_{OFF} vs Temperature (V_{IN} = 5.5 V)

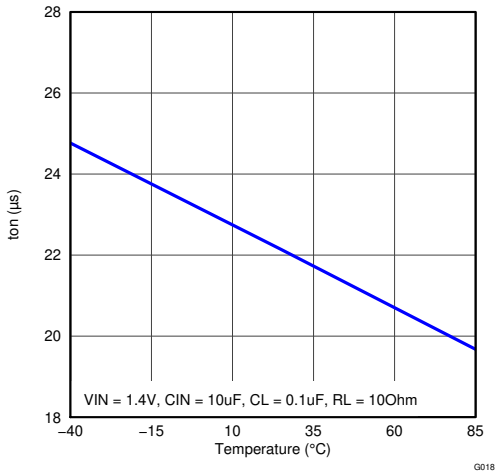


图 6-15. t_{ON} vs Temperature (V_{IN} = 1.4 V)

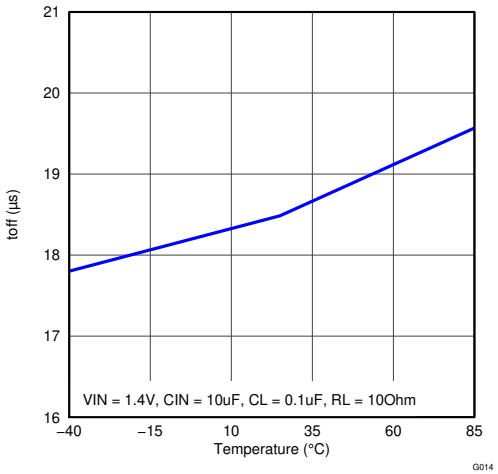


图 6-16. t_{OFF} vs Temperature (V_{IN} = 1.4 V)

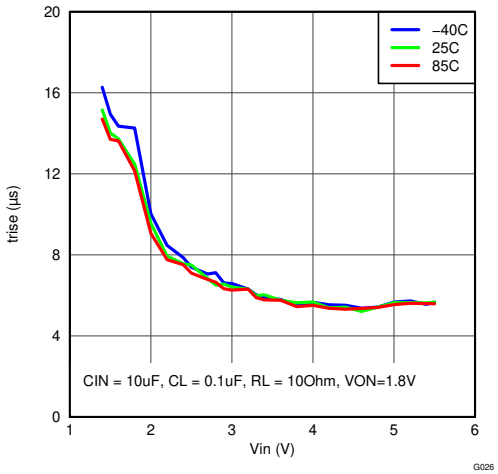


图 6-17. t_R vs V_{IN}

6.7.1 Typical AC Scope Captures at T_A = 25°C

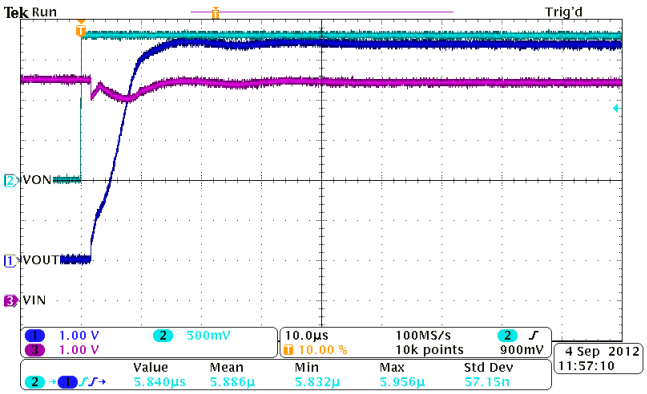


图 6-18. Turn-On Response Time (V_{IN} = 5.5 V, C_{IN} = 10 µF, C_L = 1 µF, R_L = 10 Ω)

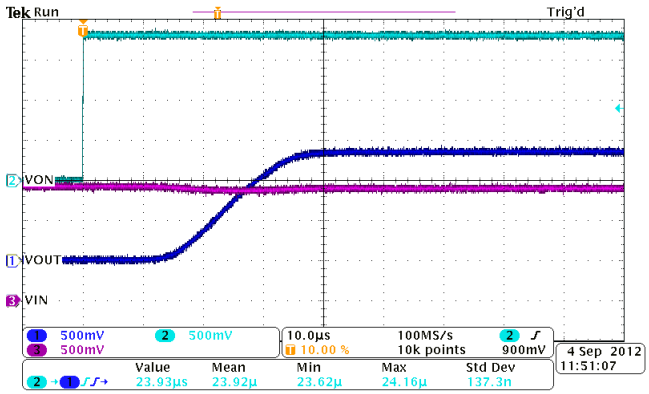


图 6-19. Turn-On Response Time (V_{IN} = 1.4 V, C_{IN} = 10 µF, C_L = 1 µF, R_L = 10 Ω)

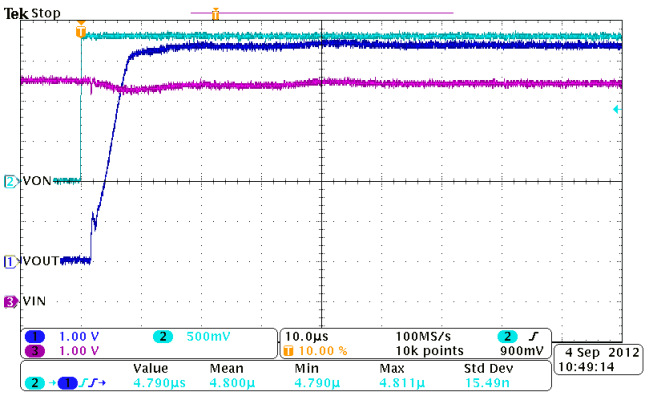


图 6-20. Turn-On Response Time (V_{IN} = 5.5 V, C_{IN} = 10 µF, C_L = 0.1 µF, R_L = 10 Ω)

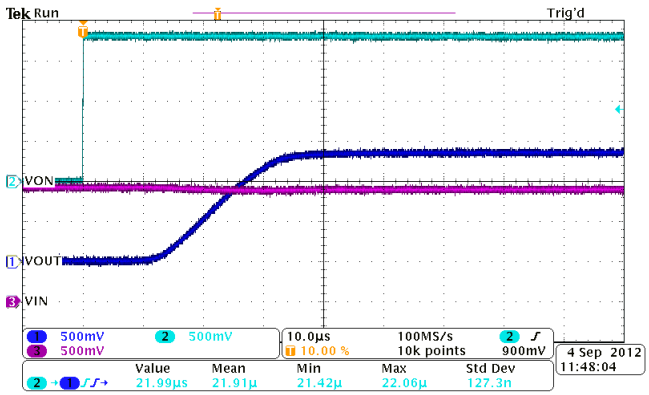


图 6-21. Turn-On Response Time (V_{IN} = 1.4 V, C_{IN} = 10 µF, C_L = 0.1 µF, R_L = 10 Ω)

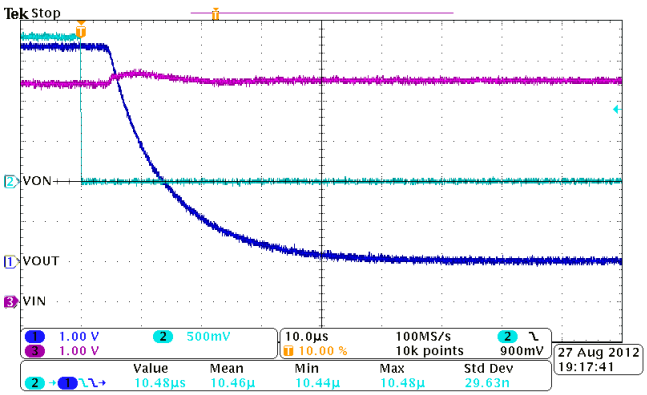


图 6-22. Turn-Off Response Time (V_{IN} = 5.5 V, C_{IN} = 10 µF, C_L = 1 µF, R_L = 10 Ω)

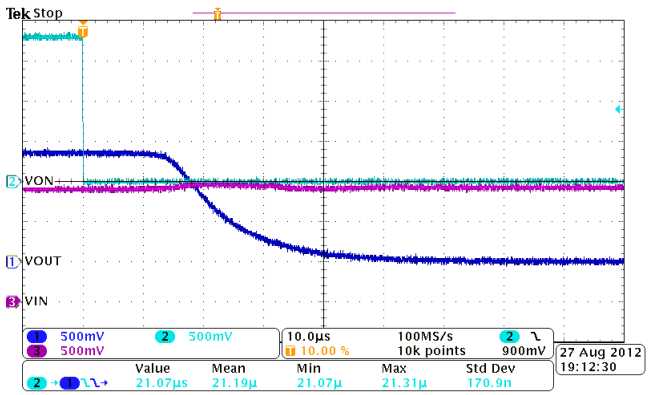


图 6-23. Turn-Off Response Time (V_{IN} = 1.4 V, C_{IN} = 10 µF, C_L = 1 µF, R_L = 10 Ω)

6.7.1 Typical AC Scope Captures at T_A = 25°C (continued)

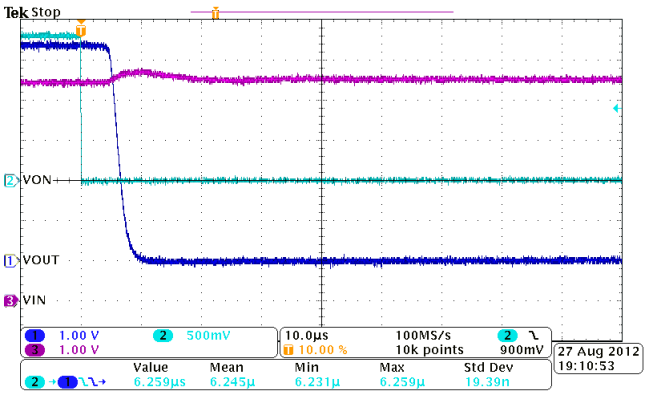


图 6-24. Turn-Off Response Time (V_{IN} = 5.5 V, C_{IN} = 10 µF, C_L = 0.1 µF, R_L = 10 Ω)

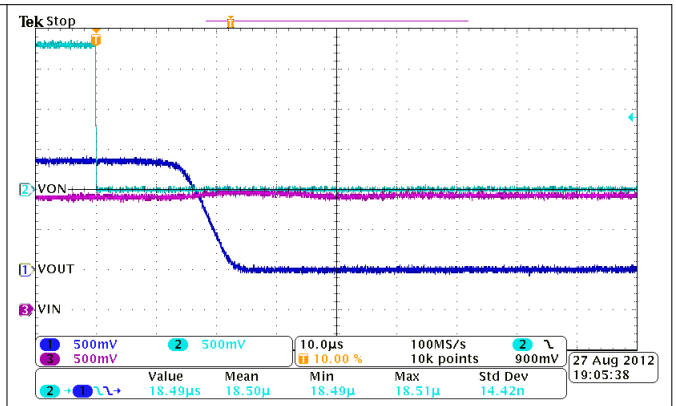
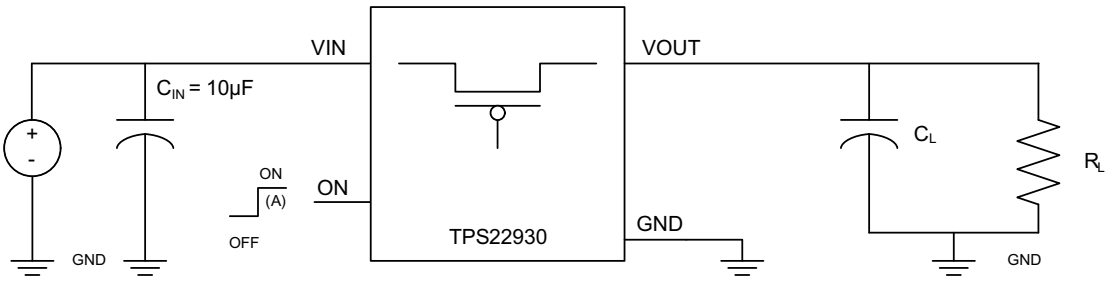
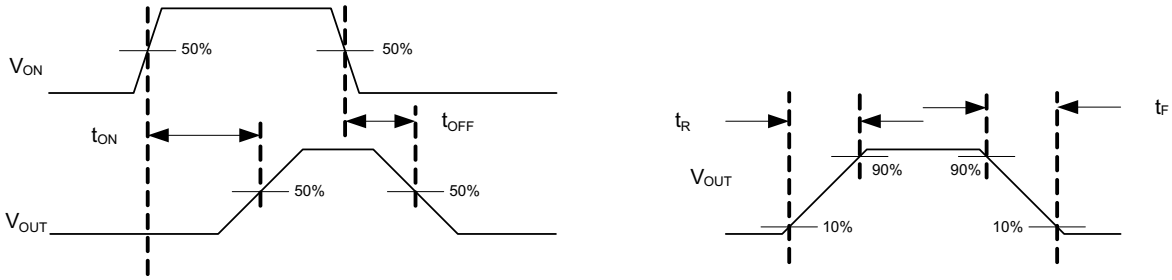


图 6-25. Turn-Off Response Time (V_{IN} = 1.4 V, C_{IN} = 10 µF, C_L = 0.1 µF, R_L = 10 Ω)

7 Parameter Measurement Information



TEST CIRCUIT



t_{ON}/t_{OFF} WAVEFORMS

(A) Rise and fall times of the control signal are 100ns.

图 7-1. Test Circuit and t_{ON}/t_{OFF} Waveforms

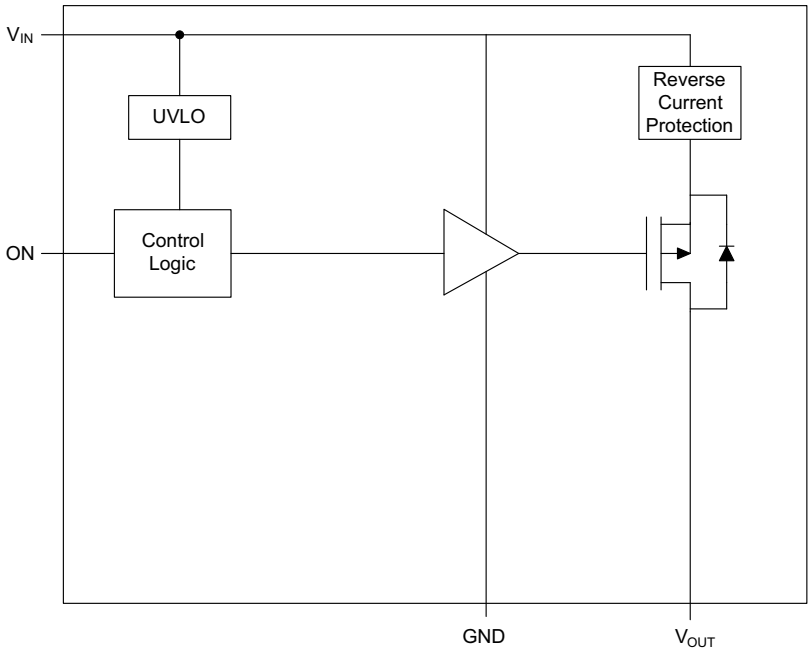
8 Detailed Description

8.1 Overview

The TPS22930 is a single channel, 2-A load switch in a 4-terminal BSGA package. A low enable threshold makes it capable of interfacing directly with low voltage control signals. In the off state, the device has very low leakage current during off state. This prevents downstream circuits from pulling high standby current from thee supply. When turning on, the output will rise with a controlled slew rate to limit inrush current.

The device will also disengage the body diode when disabled to provide reverse current protection. The undervoltage lockout (UVLO) threshold will ensure the switch is turned off and will block reverse current if the V_{IN} power supply is removed

8.2 Functional Block Diagram



8.3 Feature Description

表 8-1. Feature List

DEVICE	R_{ON} (TYP) AT 4.2 V	RISE TIME AT 4.2 V (TYP)	QUICK OUTPUT DISCHARGE(1)	MAXIMUM CONTINUOUS CURRENT	ENABLE
TPS22930A	35 mΩ	5.4 µs	No	2 A	Active High

(1) This feature discharges output of the switch to GND through a resistor, preventing the output from floating when the pass FET is disabled

8.3.1 On And Off Control

The ON pins control the state of the switch. Asserting ON high enables the switch. ON is active high and has a low threshold, making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic threshold. It can be used with any microcontroller with 1.2V or higher GPIO voltage.

8.3.2 UVLO

UVLO turns off the switch if the input voltage drops below the under voltage lockout threshold. With the ON pin active, the input voltage rising above the under voltage lockout threshold will allow a controlled turn-on of the switch to limit current over-shoot.

The maximum UVLO of the TPS22930A is 1.2 V. This is under the minimum V_{IN} voltage and meets the system UVLO requirements. Once the device is disabled through UVLO, it will block reverse current in the case a voltage is applied to V_{OUT}

8.3.3 Reverse Current Protection

Reverse current protection (RCP) is only active when ON is asserted low. When ON is asserted high, current can flow from VOUT to VIN or from VIN to VOUT. This allows the device to function as a bi-directional switch when enabled.

8.4 Device Functional Modes

表 8-2 describes the state of the switch and the reverse current protection as determined by the ON pin.

表 8-2. Switch and Reverse Current Protection State

ON	V_{IN} to V_{Out}	RCP
H	On	Off
L	Off	On

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 Input Capacitor (Optional)

To limit the voltage drop on the input supply caused by transient in-rush currents when the switch turns on into a discharged load capacitor or short-circuit, it is recommended that a capacitor be placed between VIN and GND. A 1-µF ceramic capacitor, C_{IN}, placed close to the pins, is usually sufficient. Higher values of C_{IN} can be used to further reduce the voltage drop during high-current application. When switching heavy loads, it is recommended to have an input capacitor about 100 times higher than the output capacitor to avoid excessive voltage drop; however, a 100 to 1 ratio is not required for proper functionality of the device.

9.1.2 Output Capacitor (Optional)

Due to the integrated body diode in the PMOS switch, a C_{IN} greater than C_L is highly recommended. A C_L greater than C_{IN} can cause V_{OUT} to exceed V_{IN} when the system supply is removed. This could result in current flow through the body diode from V_{OUT} to V_{IN}. A C_{IN} to C_L ratio of 100 to 1 is recommended for minimizing V_{IN} dip caused by inrush currents during startup; however, a 100 to 1 ratio is not required for proper functionality of the device.

9.2 Typical Application

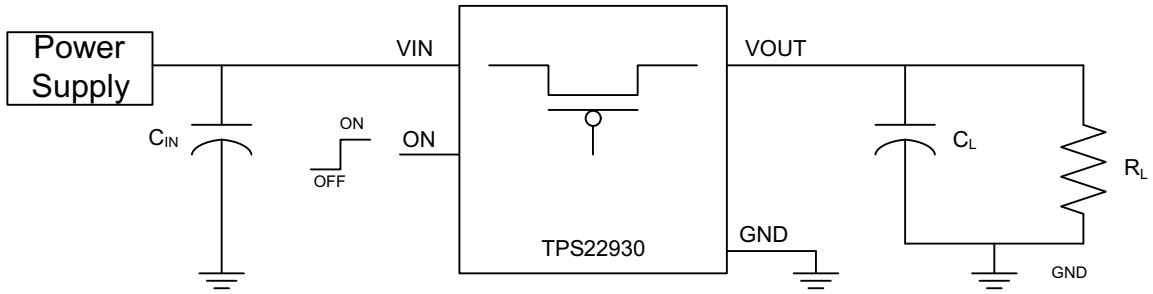


图 9-1. Typical Application Schematic

9.2.1 Design Requirements

For this design example, the following will be used as the system requirements.

表 9-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
V_{IN} Range	1.5 V to 5.5 V
UVLO Threshold	< 1.5 V
Reverse Current Protection	Requred
Load Current	1 A
Ambient Temperature	25 °C

9.2.2 Detailed Design Procedure

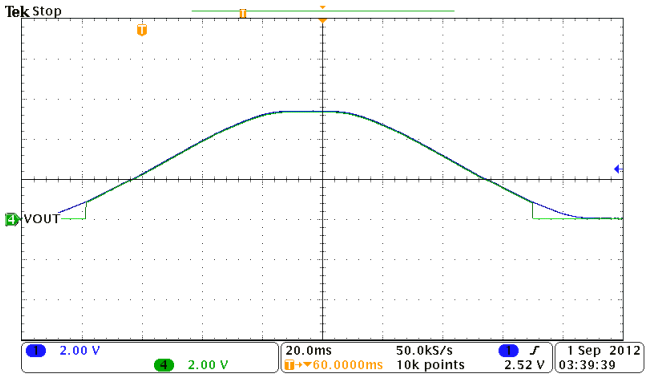
To begin the design process, the designer needs to know the following:

- Input Voltage range

- UVLO Threshold
- Load Current
- Ambient Temperature

9.2.3 Application Curve

UVLO Response shows the UVLO response when the device is enabled.



ON = 5 V

图 9-2. UVLO Response

10 Power Supply Recommendations

The device is designed to operate from a VIN range of 1.5 V to 5.5 V. The power supply should be well regulated and placed as close to the device terminals as possible. It must be able to withstand all transient and load current steps. in most situations, using an input capacitance of 1 µF is sufficient to prevent the supply voltage from dipping when the switch is turned on. In cases where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance may be required on the input

11 Layout

11.1 Layout Guidelines

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects along with minimizing the case to ambient thermal impedance. The ON pin cannot be left floating and must be driven either high or low for proper functionality.

图 11-1 shows an example of a layout.

11.2 Layout Example

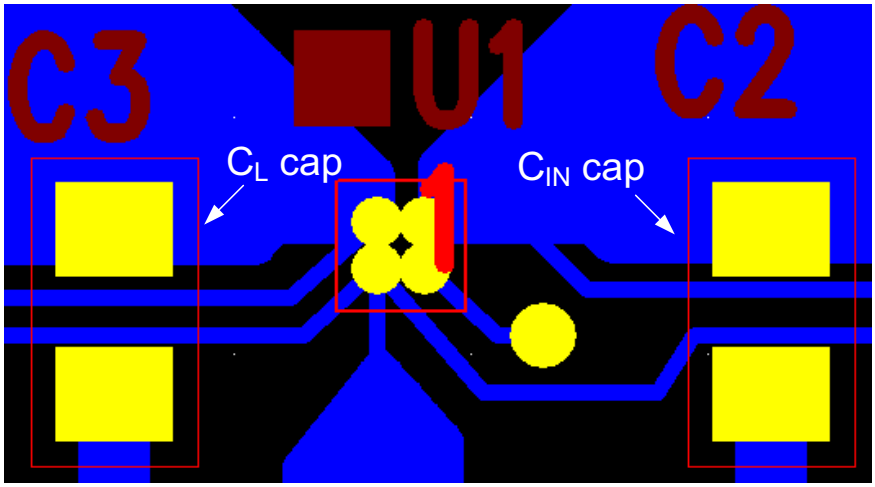


图 11-1. Layout Recommendation

11.3 Thermal Considerations

The maximum IC junction temperature should be restricted to 125°C under normal operating conditions. To calculate the maximum allowable dissipation, $P_{D(max)}$ for a given output current and ambient temperature, use the following equation as a guideline:

$$P_{D(max)} = \frac{T_{J(max)} - T_A}{\theta_{JA}} \quad (1)$$

where

- $P_{D(max)}$ = maximum allowable power dissipation
- $T_{J(max)}$ = maximum allowable junction temperature (125°C for the TPS22930)
- T_A = ambient temperature of the device
- Θ_{JA} = junction to air thermal impedance. See *Thermal Information* table. This parameter is highly dependent upon board layout.

The power dissipated by the device depends on the R_{ON} of the device at a given V_{IN}. To calculate the amount of power being dissipated by the device, use the following equation:

$$P_{IR} = I^2 \times R_{ON} \quad (2)$$

where

- P_{IR} = power dissipated by the device
- I = load current in amperes
- R_{ON} = resistance of the device in Ohms at a given V_{IN} (see *Electrical Characteristics* table)

The result from 方程式 2 should always be less than or equal to the result from 方程式 1.

12 Device and Documentation Support

12.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

12.3 Trademarks

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12.4 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.5 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

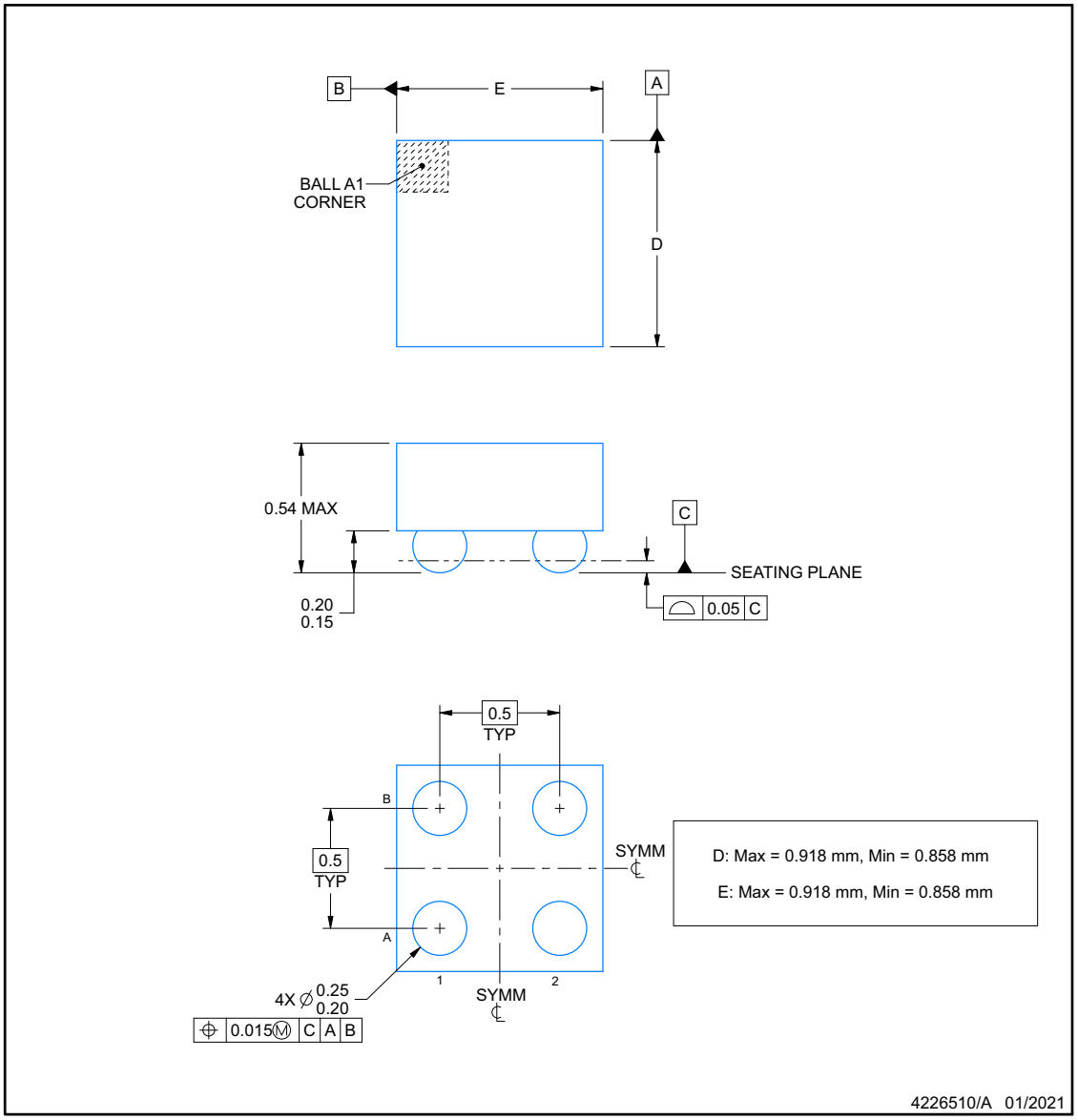
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OUTLINE

YZV0004-C01

DSBGA - 0.54 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

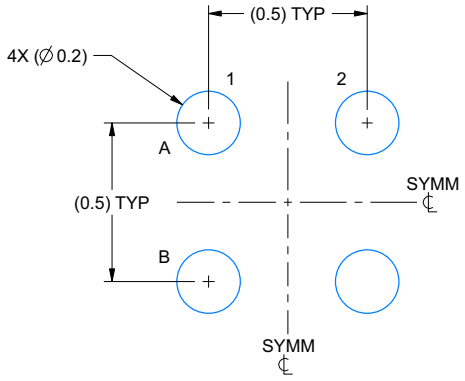
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

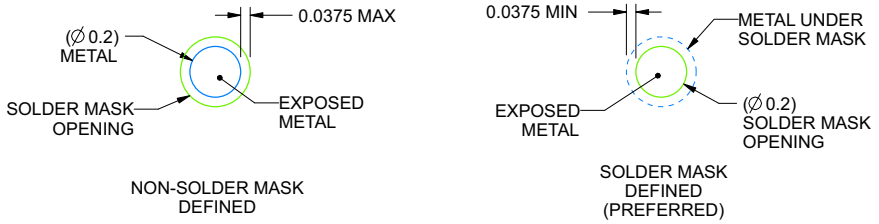
YZV0004-C01

DSBGA - 0.54 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 50X



SOLDER MASK DETAILS
NOT TO SCALE

4226510/A 01/2021

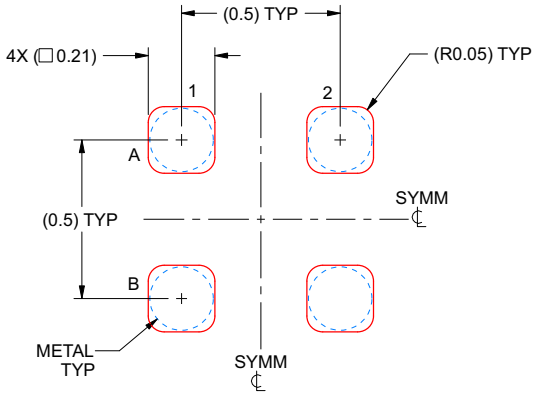
NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
   See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YZV0004-C01 **DSBGA - 0.54 mm max height**

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.075 mm THICK STENCIL
SCALE: 50X

4226510/A 01/2021

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22930AYZVR	ACTIVE	DSBGA	YZV	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	3Q	Samples
TPS22930AYZVT	ACTIVE	DSBGA	YZV	4	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	3Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

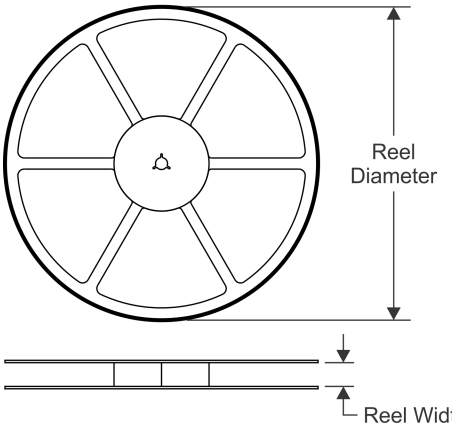
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

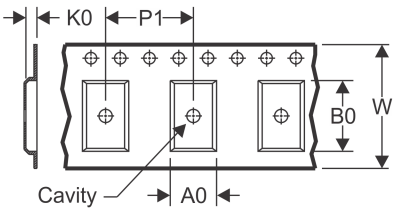
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

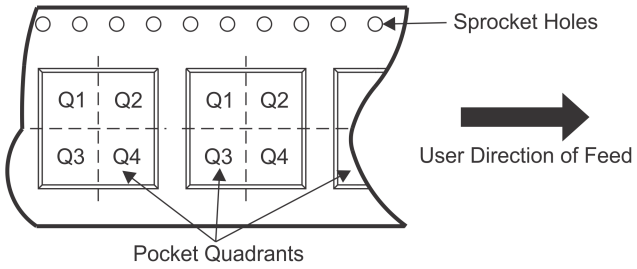


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

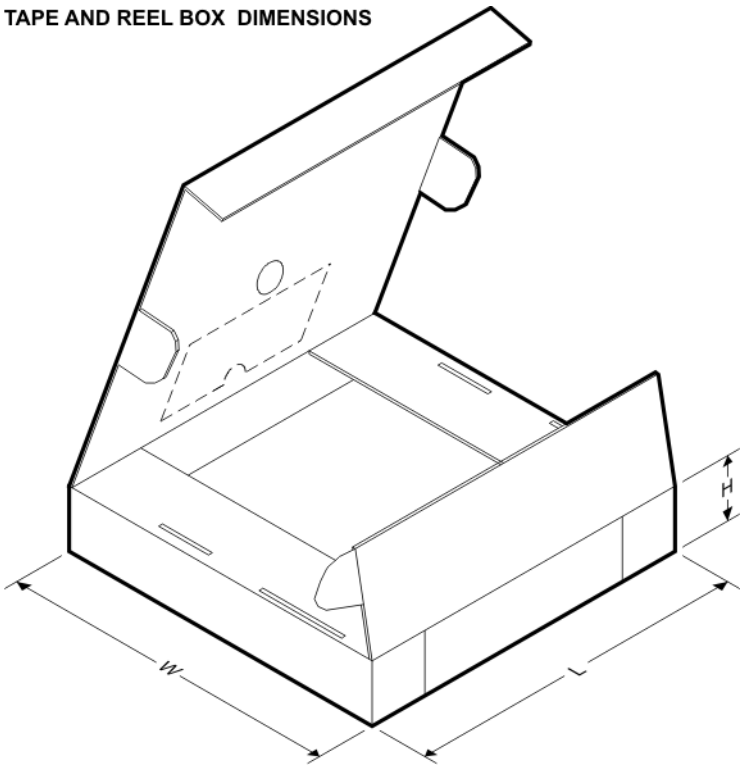
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22930AYZVR	DSBGA	YZV	4	3000	180.0	8.4	1.0	1.0	0.63	4.0	8.0	Q1
TPS22930AYZVT	DSBGA	YZV	4	250	180.0	8.4	1.0	1.0	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22930AYZVR	DSBGA	YZV	4	3000	182.0	182.0	20.0
TPS22930AYZVT	DSBGA	YZV	4	250	182.0	182.0	20.0

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